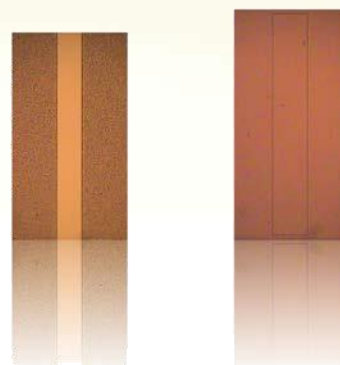


# 808nm 200mW Chip

## Introduction

808nm laser diode is packaged on standard C-Mount heat sink, or better heat sink ones, which also can be adopted in Medical Illumination, Target Indication, Laser Show, Scientific Research.



## Parameters (25°C)

808nm 200mW Chip			
Parameter		Unit	CLDM-0808-200m
Optical Parameter	Output Power $P_o$	mW	200
	Center Wavelength $\lambda_c$	nm	$808 \pm 4$
	Beam Divergence $\theta_{\perp} \times \theta_{\parallel}$	deg	40x10
	COD	W	$\geq 0.40$
Chip Size	Emitting Area	$\mu\text{m}$	28
	Period	$\mu\text{m}$	350
	Cavity Length	$\mu\text{m}$	700
Electrical Parameter	Slope Efficiency $E_s$	W/A	$\geq 0.95$
	Threshold Current $I_{th}$	A	$\leq 0.10$
	Operating Current $I_f$	A	$\leq 0.32$
	Operating Voltage $V_f$	V	$\leq 2.00$





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## Notice

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1. Item notice: CLDM( item model)-\*\*\*\*( center wavelength)-\*\*\*\*( output power)
2. Data sheet is basis on the result of under 25°C testing.
3. Data sheet is basis on the TO package testing.
4. For more information, please contact Hi-Tech Optoelectronics Co., Ltd.



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